

# DATA SHEET

**BF998WR**

**N-channel dual-gate MOS-FET**

Product specification  
Supersedes data of 1995 Apr 25

1997 Sep 05



# N-channel dual-gate MOS-FET

# BF998WR

## FEATURES

- High forward transfer admittance
- Short channel transistor with high forward transfer admittance to input capacitance ratio
- Low noise gain controlled amplifier up to 1 GHz.

## APPLICATIONS

- VHF and UHF applications with 12 V supply voltage, such as television tuners and professional communications equipment.

## DESCRIPTION

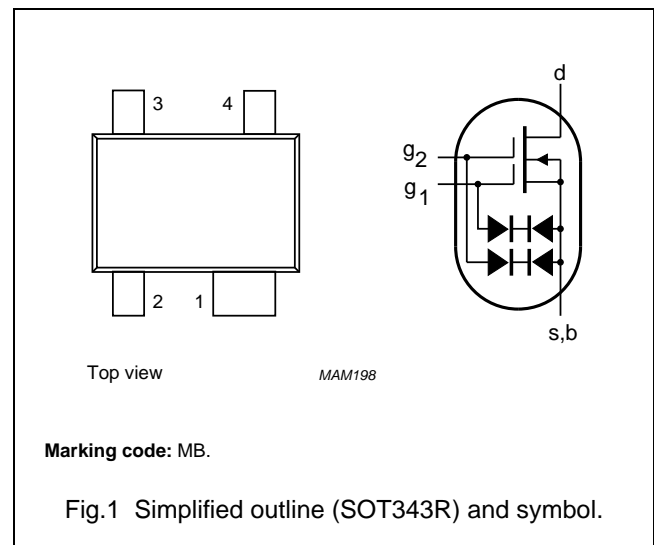
Depletion type field-effect transistor in a plastic microminiature SOT343R package with source and substrate interconnected. The transistor is protected against excessive input voltage surges by integrated back-to-back diodes between gates and source.

### CAUTION

The device is supplied in an antistatic package. The gate-source input must be protected against static discharge during transport or handling.

## PINNING

PIN	SYMBOL	DESCRIPTION
1	s, b	source
2	d	drain
3	g <sub>2</sub>	gate 2
4	g <sub>1</sub>	gate 1



## QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>DS</sub>	drain-source voltage		–	–	12	V
I <sub>D</sub>	drain current		–	–	30	mA
P <sub>tot</sub>	total power dissipation		–	–	300	mW
T <sub>j</sub>	operating junction temperature		–	–	150	°C
y <sub>fs</sub>	forward transfer admittance		–	24	–	mS
C <sub>ig1-s</sub>	input capacitance at gate 1		–	2.1	–	pF
C <sub>rs</sub>	reverse transfer capacitance	f = 1 MHz	–	25	–	fF
F	noise figure	f = 800 MHz	–	1	–	dB

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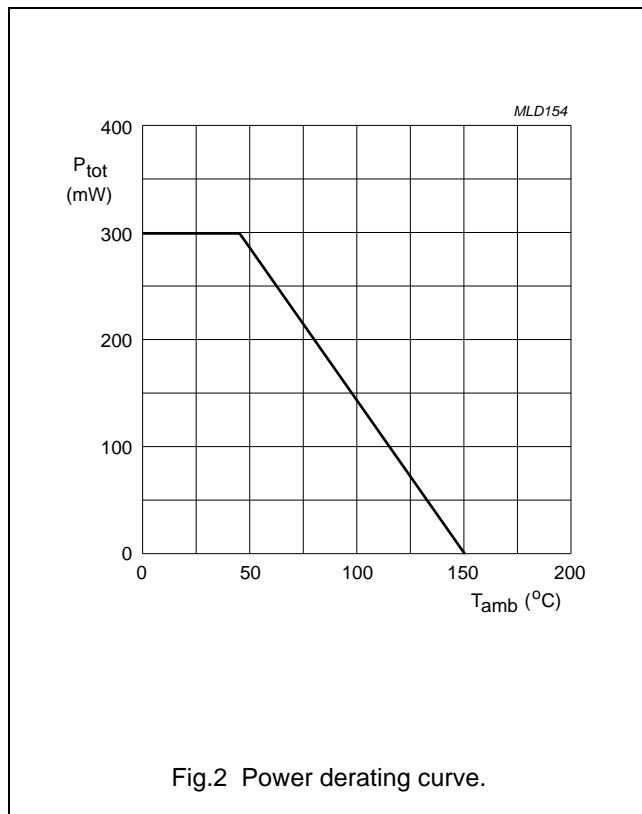
**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{DS}$	drain-source voltage		–	12	V
$I_D$	drain current		–	30	mA
$I_{G1}$	gate 1 current		–	$\pm 10$	mA
$I_{G2}$	gate 2 current		–	$\pm 10$	mA
$P_{tot}$	total power dissipation	up to $T_{amb} = 45\text{ }^{\circ}\text{C}$ ; see Fig.2; note 1	–	300	mW
$T_{stg}$	storage temperature		–65	+150	$^{\circ}\text{C}$
$T_j$	operating junction temperature		–	+150	$^{\circ}\text{C}$

**Note**

1. Device mounted on a printed-circuit board.



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## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	350	K/W
$R_{th\ j-s}$	thermal resistance from junction to soldering point	note 2; $T_s = 90\text{ °C}$	200	K/W

## Notes

1. Device mounted on a printed-circuit board.
2.  $T_s$  is the temperature at the soldering point of the source lead.

## STATIC CHARACTERISTICS

$T_j = 25\text{ °C}$ ; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{(BR)G1-SS}$	gate 1-source breakdown voltage	$V_{G2-S} = V_{DS} = 0$ ; $I_{G1-S} = 10\text{ mA}$	6	20	V
$V_{(BR)G2-SS}$	gate 2-source breakdown voltage	$V_{G1-S} = V_{DS} = 0$ ; $I_{G2-S} = 10\text{ mA}$	6	20	V
$V_{(P)G1-S}$	gate 1-source cut-off voltage	$V_{G2-S} = 4\text{ V}$ ; $V_{DS} = 8\text{ V}$ ; $I_D = 20\text{ }\mu\text{A}$	–	–2.5	V
$V_{(P)G2-S}$	gate 2-source cut-off voltage	$V_{G1-S} = 0$ ; $V_{DS} = 8\text{ V}$ ; $I_D = 20\text{ }\mu\text{A}$	–	–2	V
$I_{DSS}$	drain-source current	$V_{G2-S} = 4\text{ V}$ ; $V_{DS} = 8\text{ V}$ ; $V_{G1-S} = 0$	2	18	mA
$I_{G1-SS}$	gate 1 cut-off current	$V_{G2-S} = V_{DS} = 0$ ; $V_{G1-S} = 5\text{ V}$	–	50	nA
$I_{G2-SS}$	gate 2 cut-off current	$V_{G1-S} = V_{DS} = 0$ ; $V_{G2-S} = 5\text{ V}$	–	50	nA

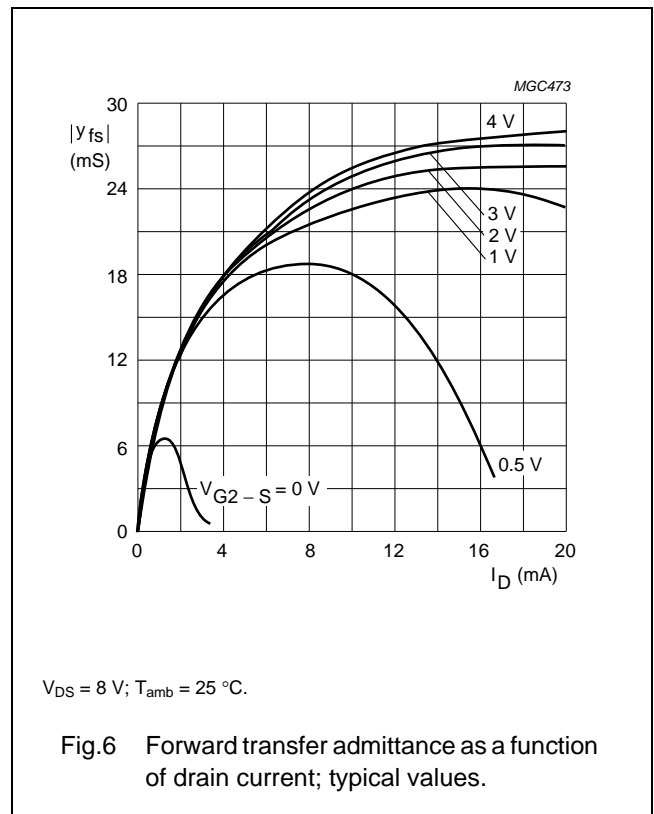
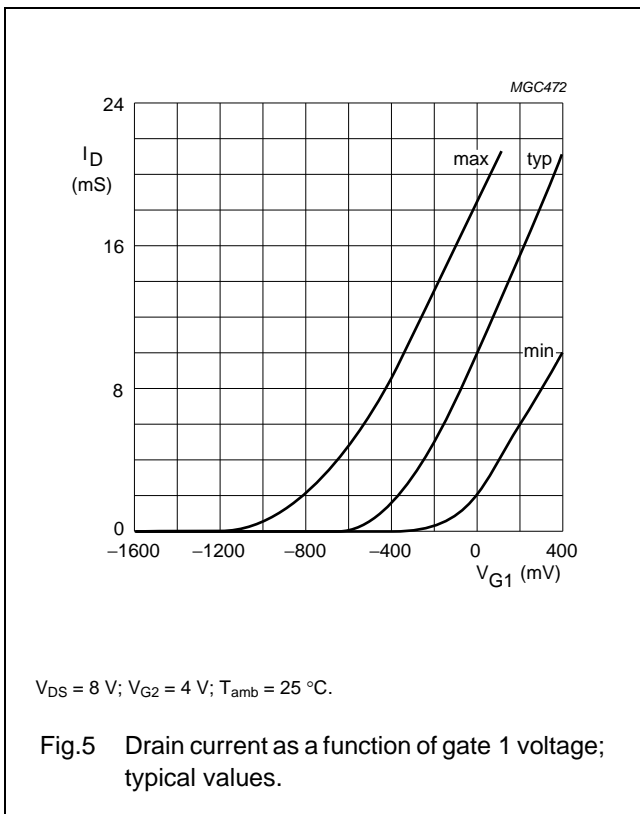
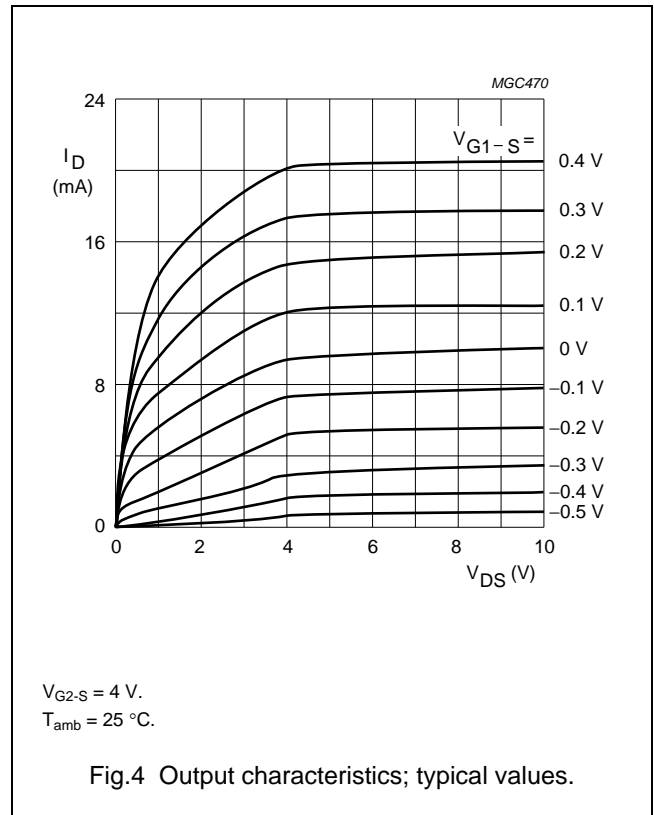
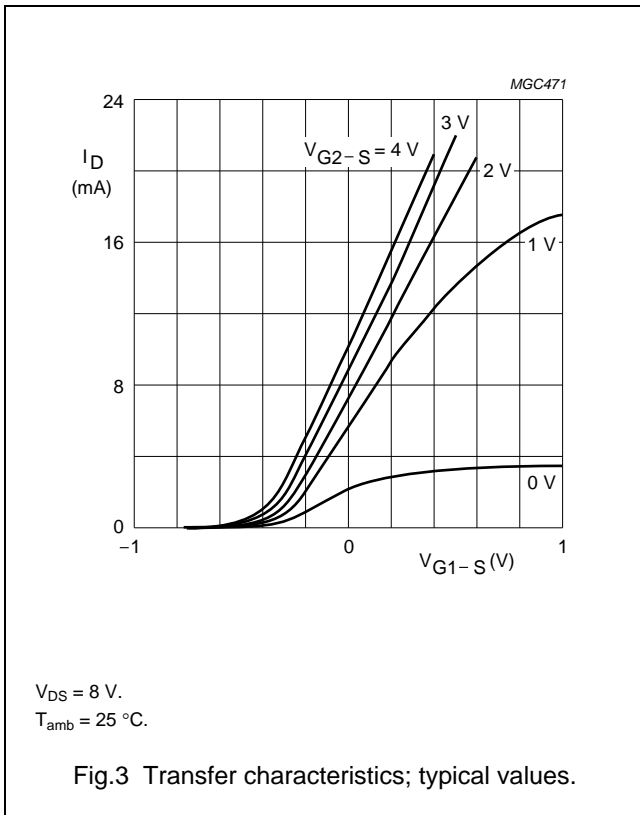
## DYNAMIC CHARACTERISTICS

Common source;  $T_{amb} = 25\text{ °C}$ ;  $V_{G2-S} = 4\text{ V}$ ;  $I_D = 10\text{ mA}$ ;  $V_{DS} = 8\text{ V}$ ; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$ y_{fs} $	forward transfer admittance	pulsed; $T_j = 25\text{ °C}$	22	25	–	mS
$C_{ig1-s}$	input capacitance at gate 1	$f = 1\text{ MHz}$	–	2.1	2.5	pF
$C_{ig2-s}$	input capacitance at gate 2	$f = 1\text{ MHz}$	–	1.2	–	pF
$C_{os}$	drain-source capacitance	$f = 1\text{ MHz}$	–	1.05	–	pF
$C_{rs}$	reverse transfer capacitance	$f = 1\text{ MHz}$	–	25	–	fF
F	noise figure	$f = 200\text{ MHz}$ ; $G_S = 2\text{ mS}$ ; $B_S = B_{Sopt}$	–	0.6	–	dB
		$f = 800\text{ MHz}$ ; $G_S = 3.3\text{ mS}$ ; $B_S = B_{Sopt}$	–	1	–	dB

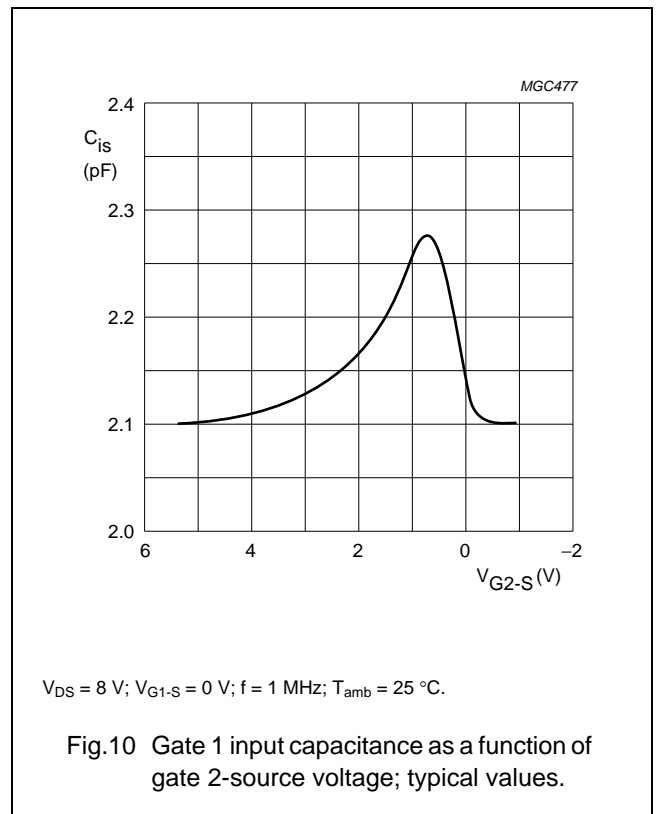
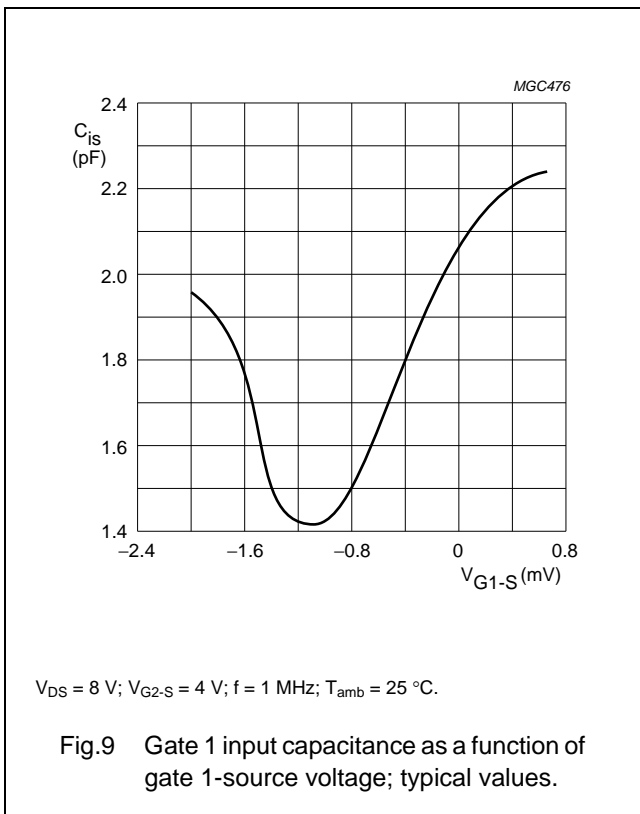
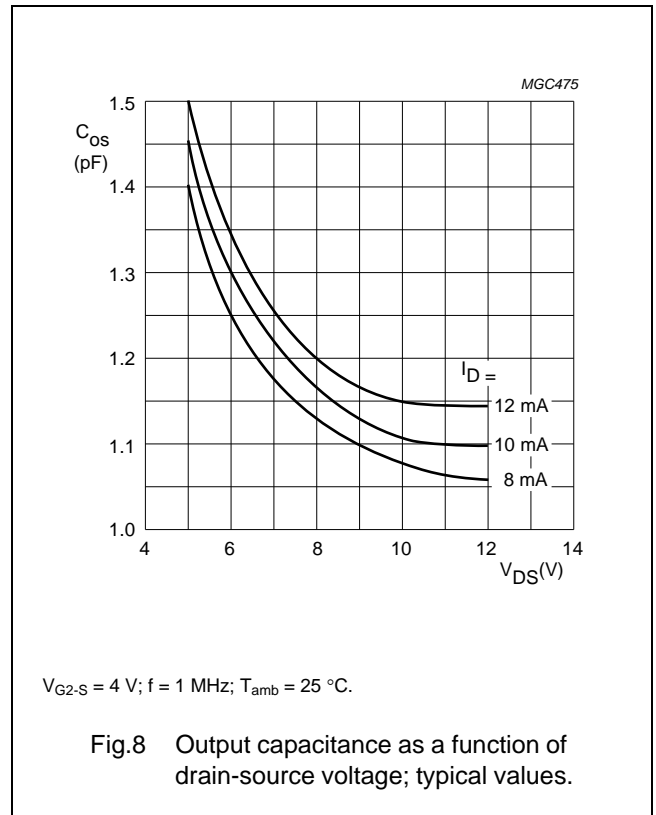
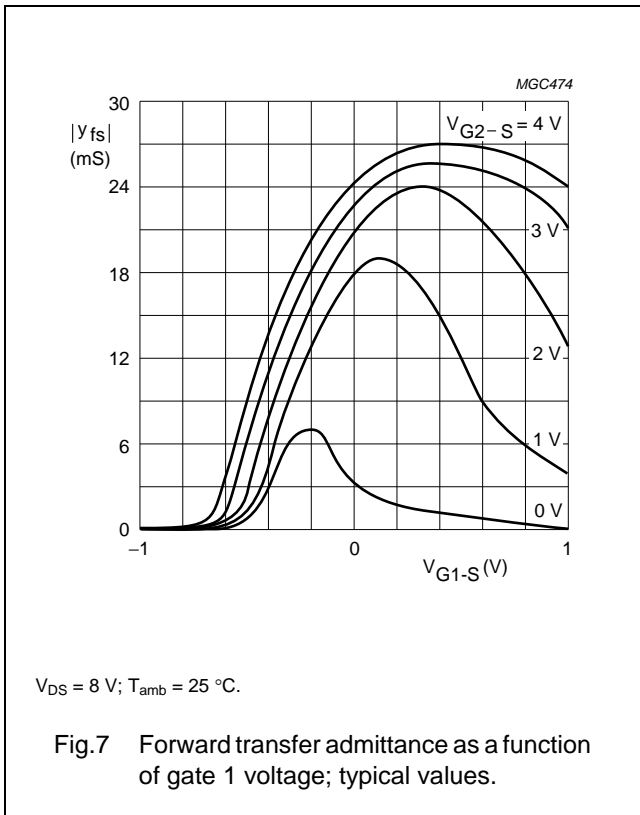
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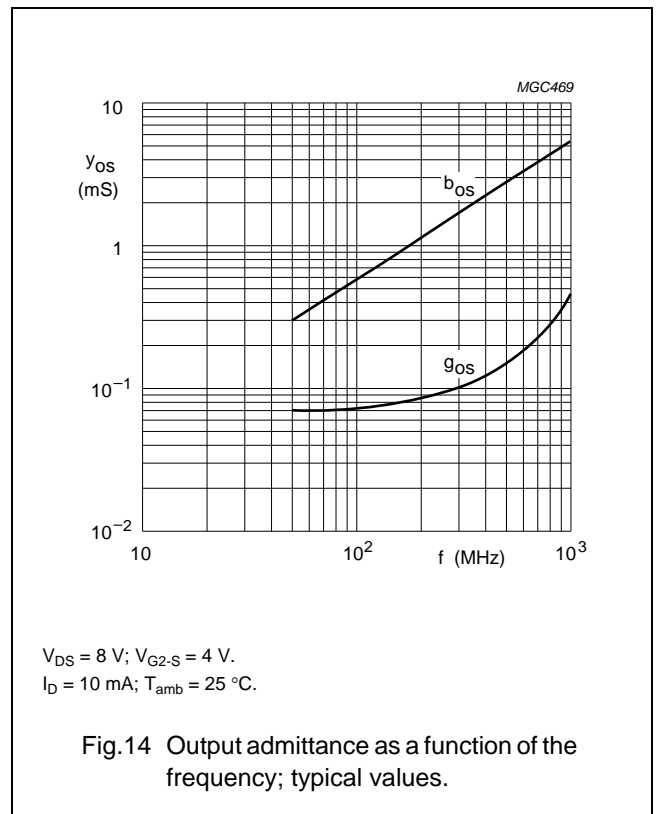
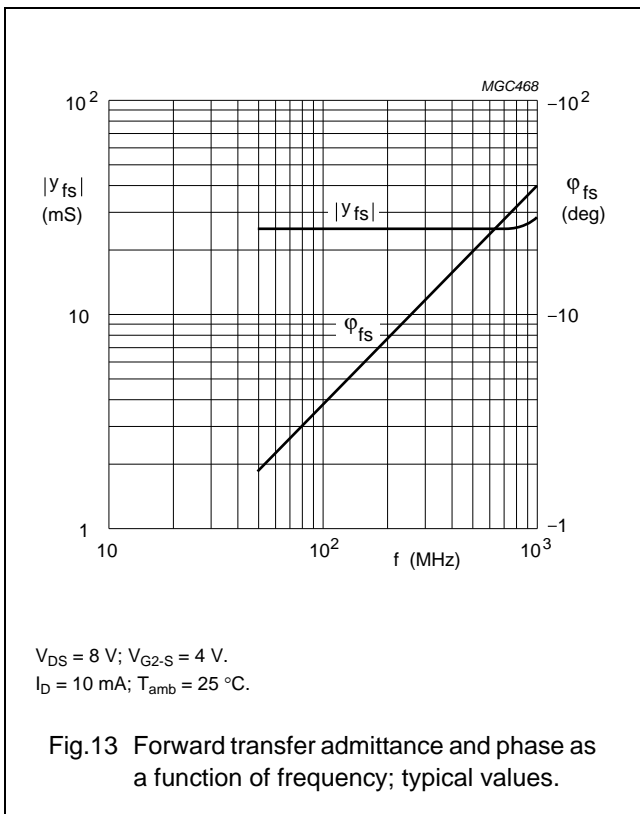
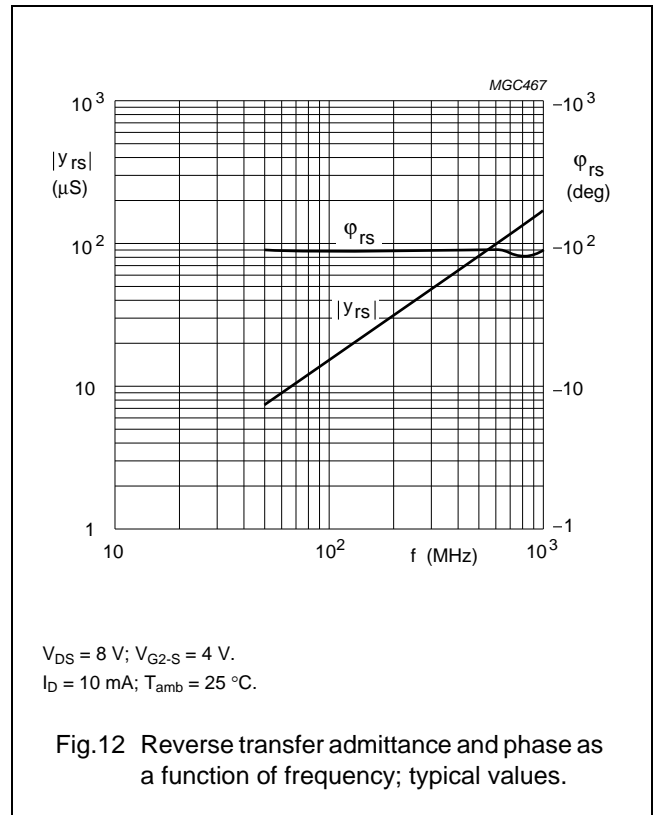
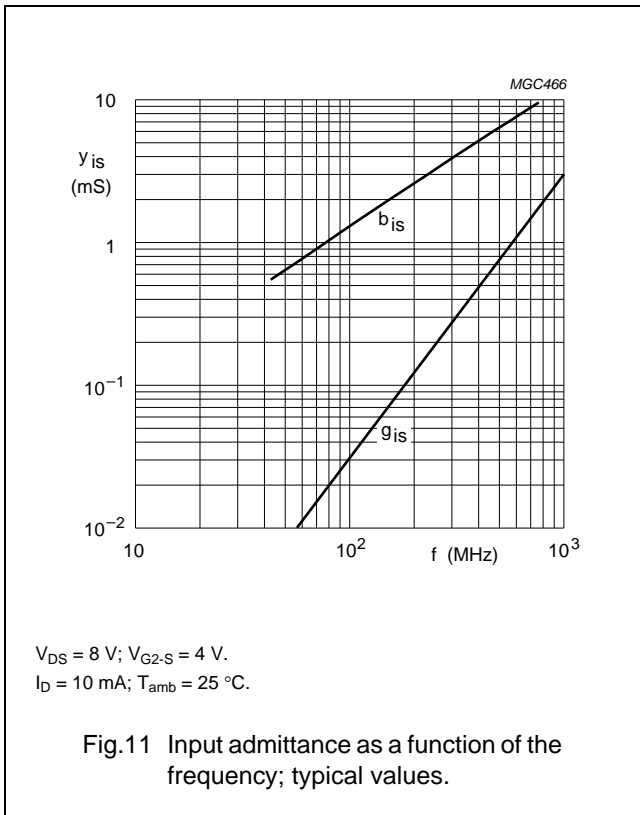
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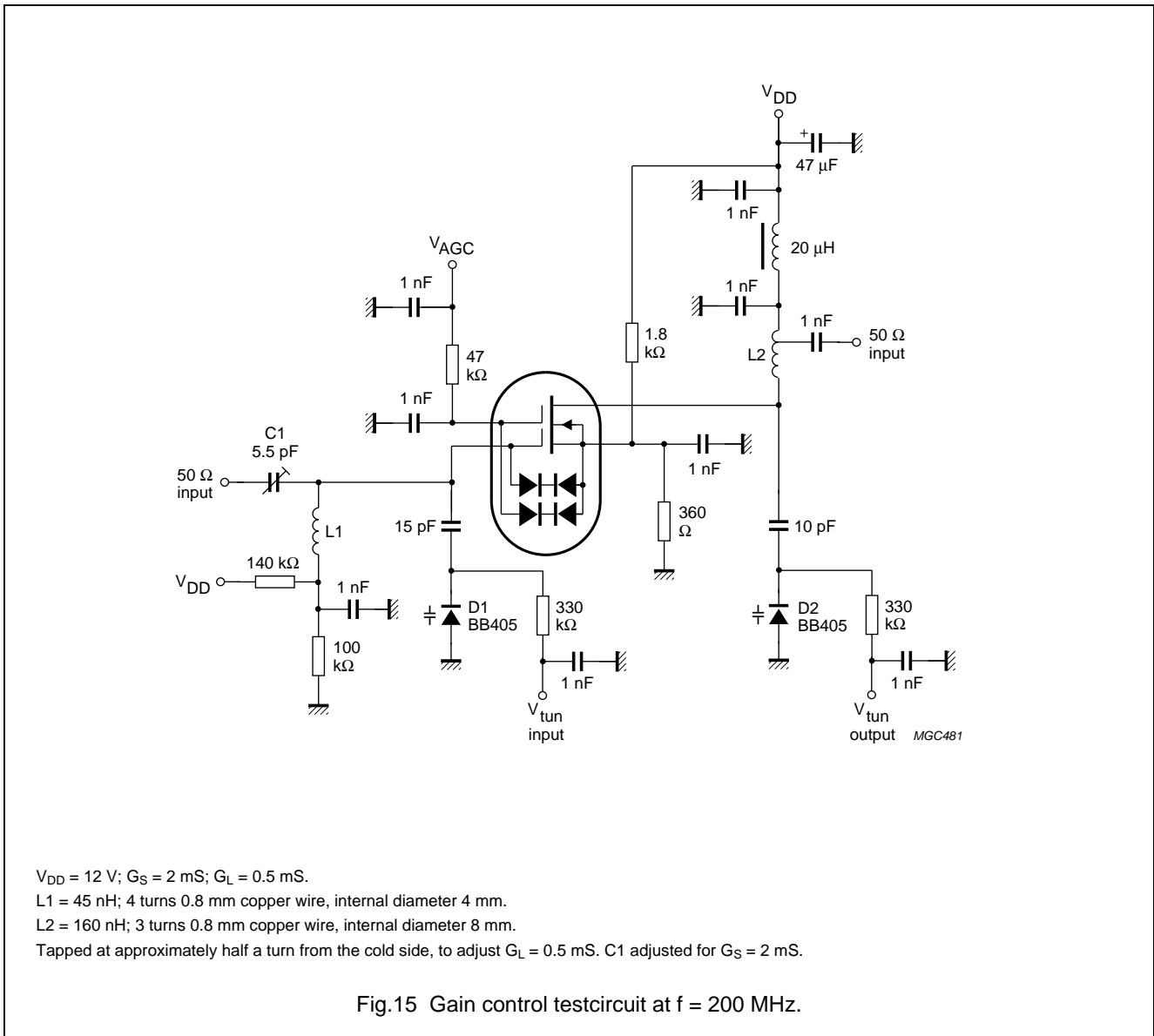
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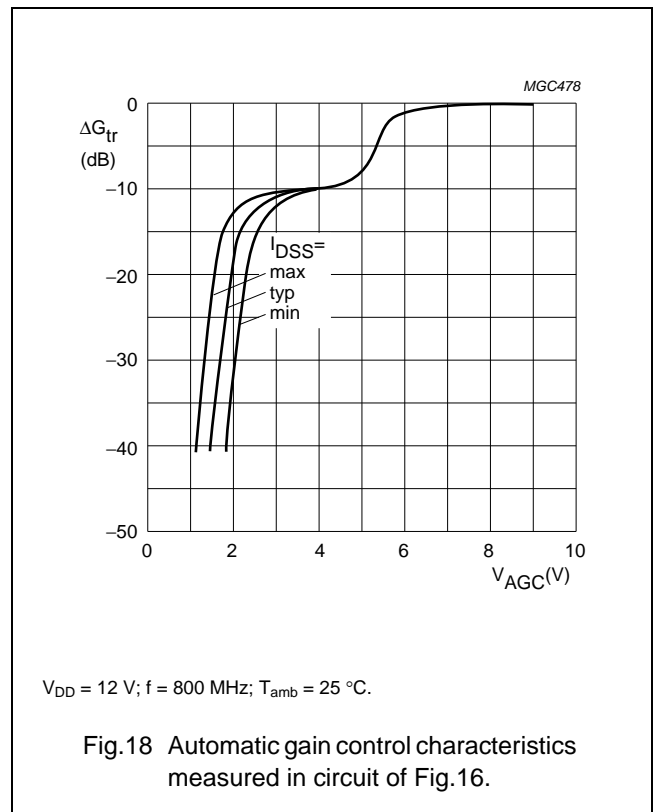
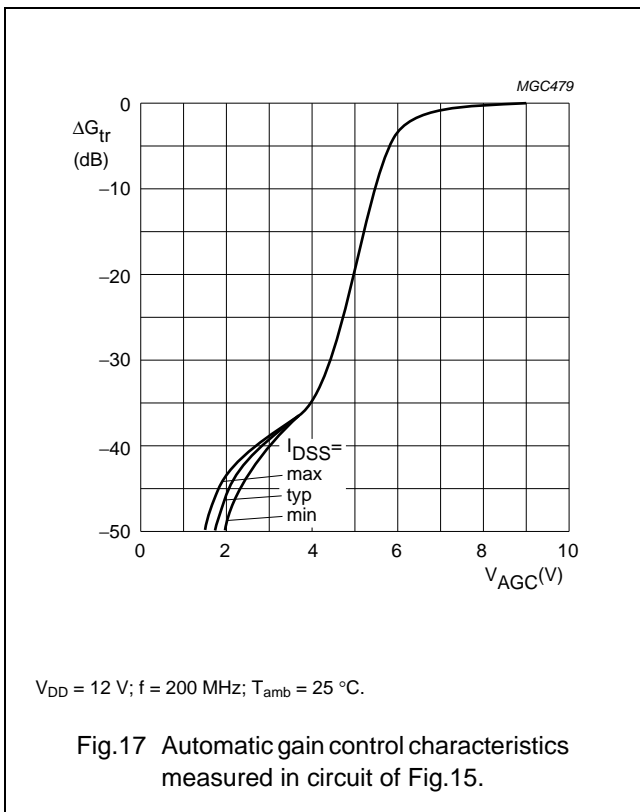
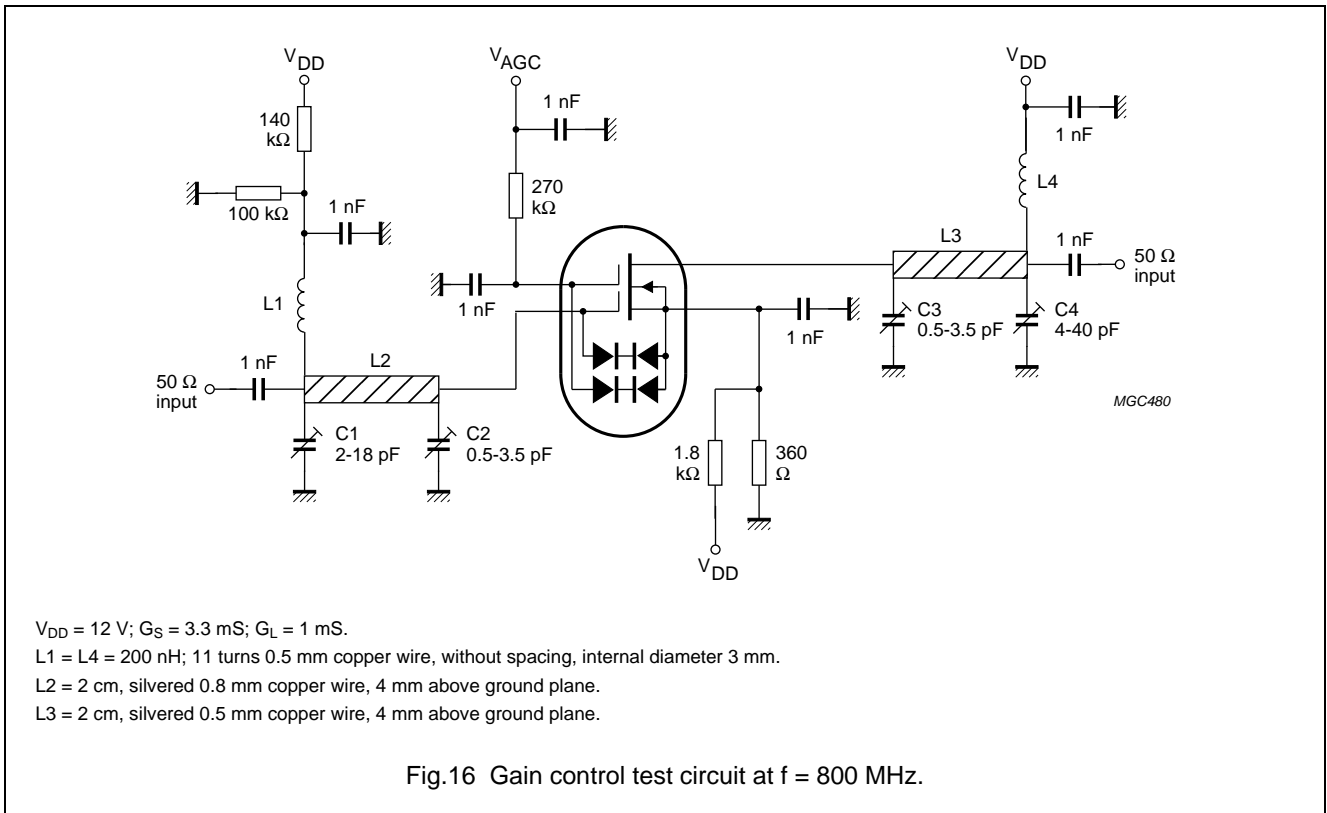
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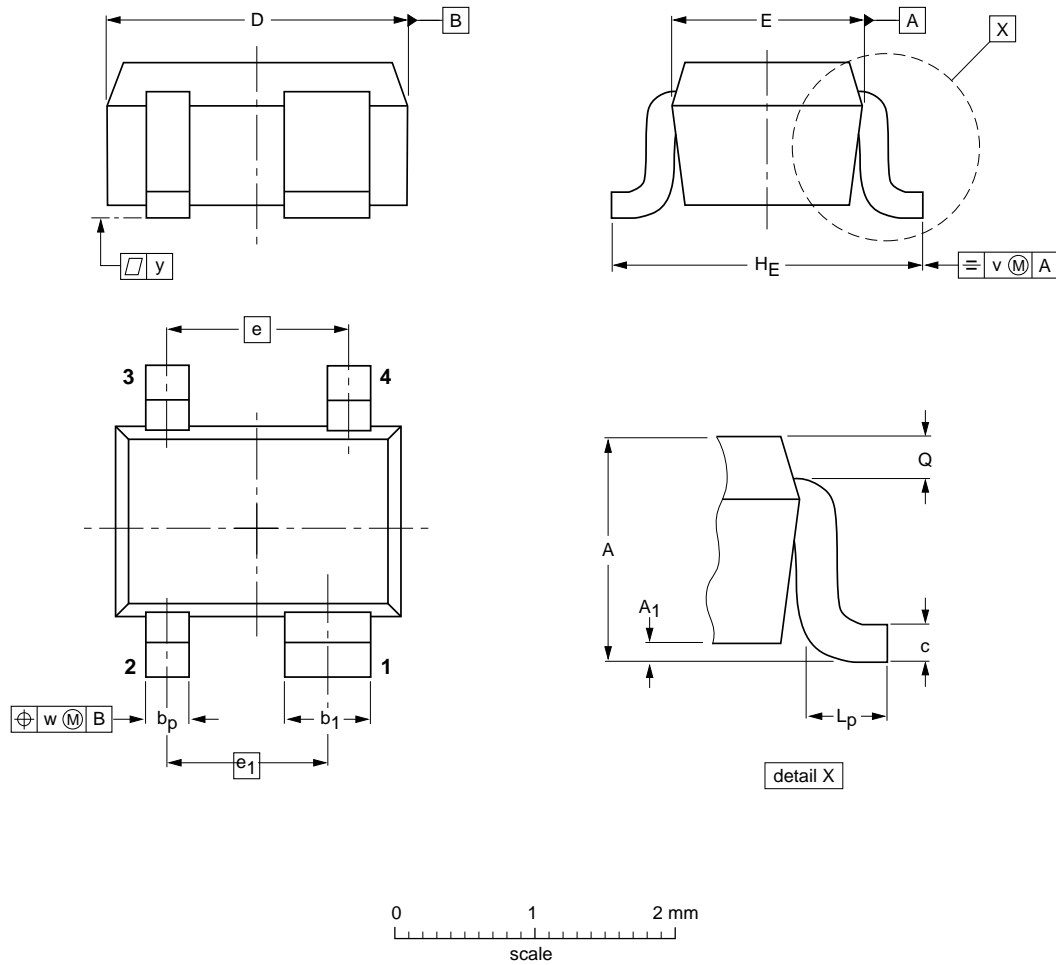
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PACKAGE OUTLINE

Plastic surface-mounted package; reverse pinning; 4 leads

SOT343R



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub> max	b <sub>p</sub>	b <sub>1</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w	y
mm	1.1 0.8	0.1	0.4 0.3	0.7 0.5	0.25 0.10	2.2 1.8	1.35 1.15	1.3	1.15	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT343R						97-05-21 06-03-16

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## DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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